Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π–MOSIII)

# 2SK2700

# Chopper Regulator, DC–DC Converter and Motor Drive Applications

• Low drain—source ON resistance :  $R_{DS}$  (ON) = 3.7  $\Omega$  (typ.) • High forward transfer admittance :  $|Y_{fs}| = 2.6 \text{ S}$  (typ.) • Low leakage current :  $I_{DSS} = 100 \mu A$  (max) ( $V_{DS} = 720 \text{ V}$ )

• Enhancement–mode :  $V_{th} = 2.0 \sim 4.0 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA})$ 

### **Maximum Ratings (Ta = 25°C)**

Characteri	stics	Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	900	V
Drain-gate voltage (Ro	<sub>GS</sub> = 20 kΩ)	$V_{DGR}$	900	V
Gate-source voltage		V <sub>GSS</sub>	±30	V
Drain current	DC (Note 1)	I <sub>D</sub>	3	Α
	Pulse (Note 1)	I <sub>DP</sub>	9	Α
Drain power dissipatio	n (Tc = 25°C)	P <sub>D</sub>	40	W
Single pulse avalanche energy (Note 2)		E <sub>AS</sub>	295	mJ
Avalanche current		I <sub>AR</sub>	3	Α
Repetitive avalanche	energy (Note 3)	E <sub>AR</sub>	4	mJ
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature ra	ange	T <sub>stg</sub>	-55~150	°C

# 1. GATE 2. DRAIN 3. SOURCE JEDEC JEITA SC-67 TOSHIBA 2.7±0.2

Weight: 1.9 g (typ.)

### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	3.125	°C/W
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	62.5	°C/W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

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Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 60.0 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 3 A

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device.

Please handle with caution.

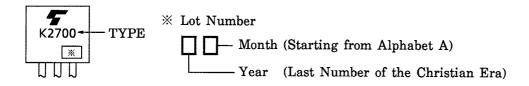
# **Electrical Characteristics (Ta = 25°C)**

Charac	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I <sub>GSS</sub>	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0 V	_	_	±10	μΑ
Gate-source bre	eakdown voltage	V <sub>(BR)</sub> GSS	$I_G = \pm 10 \ \mu A, \ V_{DS} = 0 \ V$	±30	_	_	V
Drain cut-off cur	rent	I <sub>DSS</sub>	V <sub>DS</sub> = 720 V, V <sub>GS</sub> = 0 V	_	_	100	μΑ
Drain-source bro	eakdown voltage	V <sub>(BR)DSS</sub>	$I_D$ = 10 mA, $V_{GS}$ = 0 V	900	_	_	V
Gate threshold v	roltage	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	2.0	_	4.0	V
Drain-source Of	N resistance	R <sub>DS (ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.5 A	_	3.7	4.3	Ω
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 1.5 A	0.65	2.6	_	S
Input capacitanc	е	C <sub>iss</sub>			750	_	pF
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	10	_	
Output capacitance		C <sub>oss</sub>		_	70	_	
Switching time	Rise time	t <sub>r</sub>	V <sub>GS</sub> <sub>0V</sub> I <sub>D</sub> =1.5A <sub>Out</sub> <sub>RL</sub> =133Ω	_	15	_	ns
	Turn-on time	t <sub>on</sub>		_	55	_	
	Fall time	t <sub>f</sub>		_	30	_	
	Turn-off time	t <sub>off</sub>	$V_{DD} = 200V$ $Duty \le 1\%, \ t_w = 10 \mu s$	_	110	_	
Total gate charg plus gate–drain)				25			
Gate-source charge		Q <sub>gs</sub>	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 3 \text{ A}$		13	_	nC
Gate-drain ("miller") Charge		$Q_{gd}$			12	_	

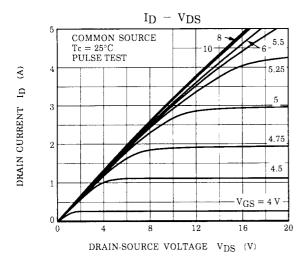
# Source-Drain Ratings and Characteristics (Ta = 25°C)

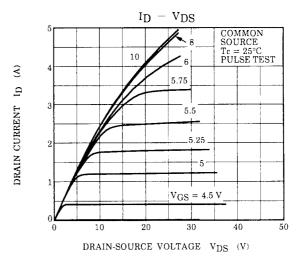
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	-	_	_	3	Α
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	-	_	_	9	Α
Forward voltage (diode)	V <sub>DSF</sub>	I <sub>DR</sub> = 3 A, V <sub>GS</sub> = 0 V	_	_	-1.9	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 3 A, V <sub>GS</sub> = 0 V	_	1100	_	ns
Reverse recovery charge	Q <sub>rr</sub>	dI <sub>DR</sub> / dt = 100 A / μs	_	7.2	_	μC

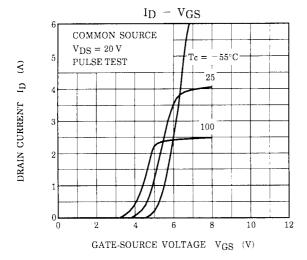
# Marking

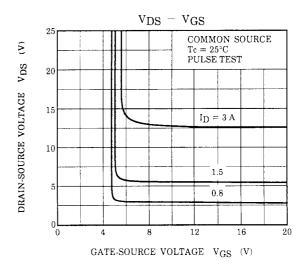


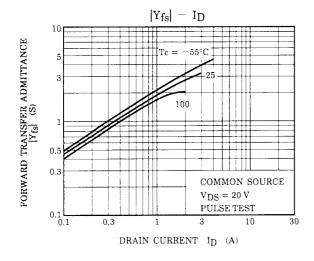
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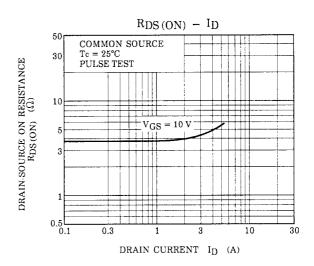




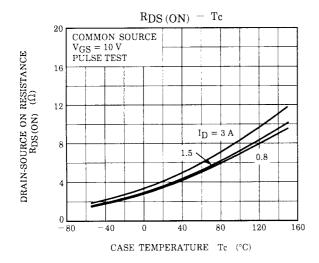


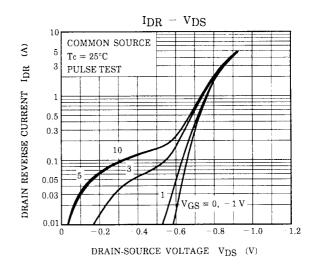


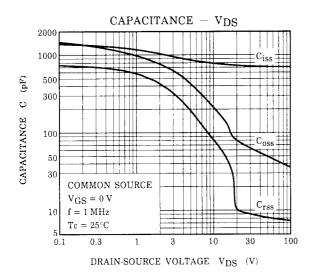


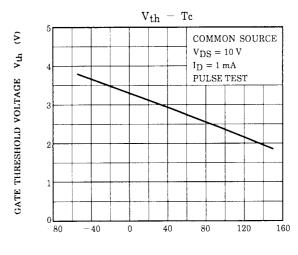


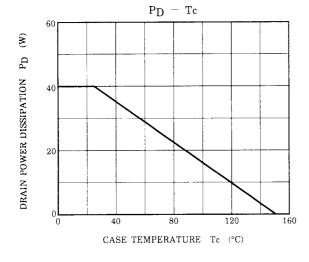
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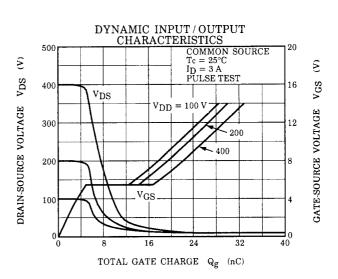




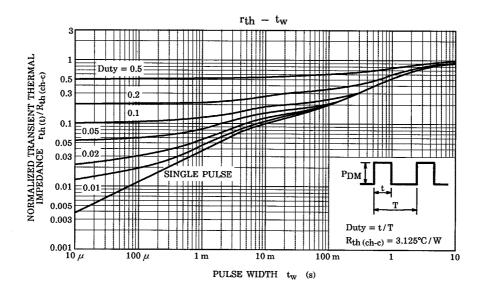


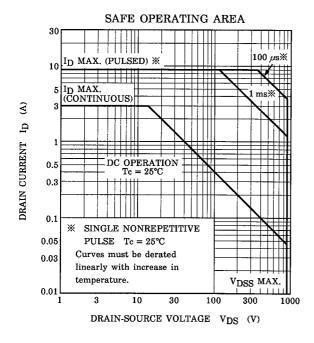


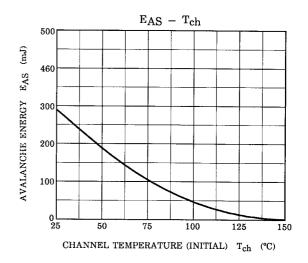


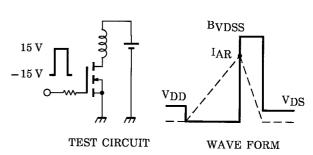


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$$R_G = 25 \Omega$$
  
 $V_{DD} = 90 \text{ V}, L = 60 \text{ mH}$ 

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^{2} \cdot \left( \frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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